



BSB053N03LP G Information



For Reference Only

Part Number BSB053N03LP G
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 71A 2WDSON

Package 3-WDSON

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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BSB053N03LP G Specifications

Manufacturer Part Number BSB053N03LP G Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 3-WDSON Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 17A (Ta), 71A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2700pF @ 15V Vgs (Max) ±2V FET Feature - Power Dissipation (Max) 2.3W (Ta), 42W (Tc) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 30A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MG-WDSON-2, CanPAK M? Package / Case 3-WDSON		
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Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C17A (Ta), 71A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 250μAGate Charge (Qg) (Max) @ Vgs29nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2700pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.3W (Ta), 42W (Tc)Rds On (Max) @ Id, Vgs5.3 mOhm @ 30A, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageMG-WDSON-2, CanPAK M?Package / Case3-WDSON	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 17A (Ta), 71A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2700pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.3W (Ta), 42W (Tc) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 30A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MG-WDSON-2, CanPAK M? Package / Case 3-WDSON	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Son (Max) @ Jd, Vgs The properature Supplier Device Package MG-WDSON-2, CanPAK M? Package / Case 2.2V @ 250μA 2.2P (250μA 2.2P (250μA 2.2P (2700pF @ 15V	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 2.2V @ 250μA 2.2P @ 10V 2700pF @ 15V 27	Current - Continuous Drain (Id) @ 25°C	17A (Ta), 71A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2700pF @ 15V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 5.3 mOhm @ 30A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MG-WDSON-2, CanPAK M? Package / Case	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MG-WDSON-2, CanPAK M? Package / Case 2700pF @ 15V 2700pF	Vgs(th) (Max) @ Id	2.2V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2.3W (Ta), 42W (Tc)Rds On (Max) @ Id, Vgs5.3 mOhm @ 30A, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageMG-WDSON-2, CanPAK M?Package / Case3-WDSON	Gate Charge (Qg) (Max) @ Vgs	29nC @ 10V
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Rds On (Max) @ Id, Vgs5.3 mOhm @ 30A, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageMG-WDSON-2, CanPAK M?Package / Case3-WDSON	FET Feature	-
Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MG-WDSON-2, CanPAK M? Package / Case 3-WDSON	Power Dissipation (Max)	2.3W (Ta), 42W (Tc)
Mounting Type Surface Mount Supplier Device Package MG-WDSON-2, CanPAK M? Package / Case 3-WDSON	Rds On (Max) @ Id, Vgs	5.3 mOhm @ 30A, 10V
Supplier Device Package MG-WDSON-2, CanPAK M? Package / Case 3-WDSON	Operating Temperature	-40°C ~ 150°C (TJ)
Package / Case 3-WDSON	Mounting Type	Surface Mount
	Supplier Device Package	MG-WDSON-2, CanPAK M?
Report errors?	Package / Case	3-WDSON
		Report errors?

BSB053N03LP G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

BSB053N03LP G Payment Methods



















BSB053N03LP G Shipping Methods













If you have any question about BSB053N03LP G, please do not hesitate to contact us!

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